TECHNICAL DATA DATA SHEET 521, REV. A

# SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop 200°C Operating Temperature

# **Applications:**

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging
- Out Performs 100 Volt Ultrafast Rectifiers

# **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	V
Max. Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle, rectangular wave form	30	А
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave (1)	570	А
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C}, \ I_{AS} = 0.75  A, \\ L = 40  \text{mH}$	11.25	mJ
Repetitive Avalanche Current	l <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 μs $f$ limited by $T_J$ max $V_A$ =1.5 $V_R$	0.75	А
Max. Junction Temperature	$T_J$	-	-65 to +200	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +200	°C

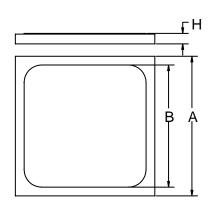
#### **Electrical Characteristics:**

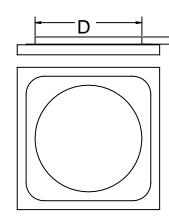
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.84	V
	$V_{F2}$	@ 30A, Pulse, T <sub>J</sub> = 125 °C	0.68	V
Max. Reverse Current	$I_{R1}$	@V <sub>R</sub> = 100V, Pulse,	750	μΑ
		T <sub>J</sub> = 25 °C		
	$I_{R2}$	@V <sub>R</sub> = 100V, Pulse,	15	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C$	1000	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

(1) in SHD package

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### Mechanical Dimensions: In Inches / mm





Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization

A = AI - 25 kÅ minimum

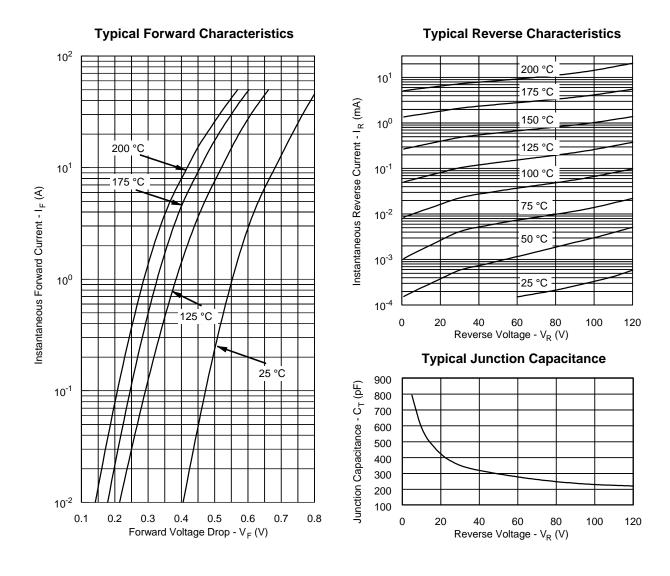
B = Ag -30 kÅ minimum

C= Au plated Ni-Moly disc with bare edge

Bottom side is cathode, top side is anode.

A	В	D	Н	h
$0.175 \pm 0.003$	$0.163 \pm 0.003$	$.120 \pm 0.003$	$0.0105 \pm 0.001$ , for Al top	$.011\pm0.0008$
$(4.45 \pm 0.077)$	$(4.14 \pm 0.077)$		$0.0155 \pm 0.001$ , for Ag top	

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